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Publications:

1. **Sneha Kabra**, Harsupreet Kaur, Ritesh Gupta, Subhasis Haldar, Mridula Gupta and R.S.Gupta “A Semi Empirical Approach for Submicron GaN MESFET Using an Accurate Velocity Field Relationship for High Power Applications”, **Microelectronics Journal**, pp.620-626, no.7, vol.37, 2006.
2. **Sneha Kabra**, Harsupreet Kaur, Subhasis Haldar, Mridula Gupta and R. S. Gupta “An Analytical Model for GaN MESFET’s Using New Velocity-Field Dependence” **Physica Status Solidi C**, pp. 2350-2355, no.6, vol.3, 2006.
3. **Sneha Kabra**, Harsupreet Kaur, Subhasis Haldar, Mridula Gupta and R. S. Gupta, “Two Dimensional Subthreshold Analysis of Sub-Micron GaN MESFET” **Microelectronics Journal**, vol. 38, no. 4-5, pp. 547–555, 2007.
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5. **Sneha Kabra**, Harsupreet Kaur, Subhasis Haldar, Mridula Gupta and R. S. Gupta, “Temperature Dependent Analytical Model of sub-micron GaN MESFETs for Microwave Frequency Applications”, **Solid State Electronics**, vol.52, no.1, pp.25-30, 2008.
6. Harsupreet Kaur, **Sneha Kabra**, Subhasis Haldar, and R. S. Gupta, “Impact of graded channel (GC) design in fully depleted cylindrical/surrounding gate MOSFET (FD CGT/SGT) for improved short channel immunity and hot carrier reliability” **Solid State Electronics**, vol. 51, pp. 398-404, 2007.
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9. Impact of laterally asymmetric channel and gate stack architecture on device performance of surrounding gate MOSFETs Harsupreet Kaur, **Sneha Kabra**, S Haldar, RS Gupta - Microwave and Optical Technology Letters, vol52, no.3, pp. 746-750, 2010
10. Sona P Kumar, Anju Agrawal, **Sneha Kabra**, Mridula Gupta and R.S.Gupta “An analysis for AlGa_N/Ga_N modulation doped field effect transistor using accurate velocity-field dependence for high power microwave frequency applications” **Microelectronics Journal**, vol.37, pp. 1339-1346, 2006.
11. Threshold voltage model for small geometry AlGa_N/Ga_N HEMTs based on analytical solution of 3-D Poisson's equation, Sona P Kumar, A Agrawal, R Chaujar, **Sneha Kabra**, M Gupta, Microelectronics Journal, Vol38 no.10, pp 1013-1020, 2007
12. Development of e-resource on standard procedure of operation and applications of important electronic devices used by undergraduate science students **Sneha Kabra**, Amita Kapoor, Himani Dua, DU Journal of Undergraduate Research and Innovation, 2015